Design of 8x8 SRAM based on 6T SRAM cell

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Abstract - SRAM forms a storage element in VLSI chips due to their large storage density and small access time. The Scope of the work is to design a 6 transistor SRAM cell along with a 3x8 Decoder and finally integrating the analog block along with digital block to form a mixed signal based 8x8 SRAM.

Keywords – 6T SRAM, CMOS, PMOS, NMOS

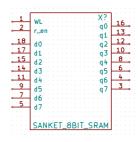
1.INTRODUCTION

Memory components are particularly significant in contemporary computers for storing vast quantities of data. Because we all know that SRAM is considerably quicker than DRAM, we have the notion of caching the memory, which means that we save the data in SRAMs on the initial load so that the subsequent load time is greatly reduced. The key benefits of employing SRAM are its fast switching speed and low power usage. This circuit's uses include a basic memory element, a Lookup table for an FPGA, and so on. Because servers are normally turned on all the time, SRAMs are commonly employed in server-based online applications. Because the use of this SRAM is projected to develop further, we will create an 8x8-Bit SRAM-based cache memory that will be primarily employed due to high performance and low consumption in contrast to DRAM.

2.CIRCUIT DETAILS

1.Decoder

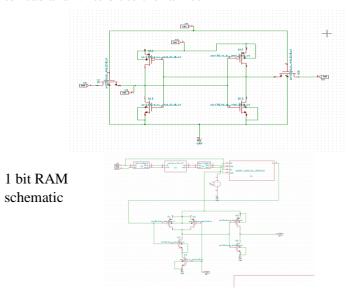
Decoder in digital electronics does the job of decoding based on the input data. Decoder on n input will have 2ⁿ outputs. The output is purely base on the combinational logic inside it. In this paper Decoder will be representing the digital block of mixed signal Design.



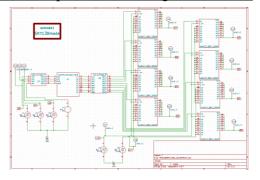
| A,B,C | y0,y1,y2,y3,y4,y5,y6,y7 |
|-------|-------------------------|
| 000 | 00000001 |
| 001 | 00000010 |
| 010 | 00000100 |
| 011 | 00001000 |
| 100 | 00010000 |
| 101 | 00100000 |
| 110 | 01000000 |
| 111 | 10000000 |
| | |

2. 6T 1 bit RAM cell

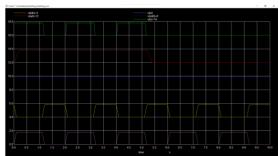
The proposed design of SRAM is made of 6 transistors, pins associated with the design are BL,BLB,WL.WL pin is used to control Read/Write and Hold operation. BL,BLB are used to read and write bit to the ram cell



3.8X8 RAM implementation along with Decoder



3.OUTPUT WAVEFORM OF 6T RAM CELL



4.REFERENCES

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